



7N65 7N65F 7N65D 7N65E 7N65M 7N65N 650V N-Channel Power MOSFET

FEATURES

- $R_{DS(ON)} < 1.5\Omega$ @ $V_{GS} = 10V$
- Fast switching capability
- Low gate charge
- Lead free in compliance with EU RoHS directive.
- Green molding compound

MECHANICAL DATA

- Case: TO-220, ITO-220, TO-263, TO-262 Package
- TO-251, TO-252 Package

Ordering Information

Part No.	Package	Packing
7N65-TU	TO-220	50pcs / Tube
7N65F-TU	ITO-220	50pcs / Tube
7N65E-TU	TO-262	50pcs / Tube
7N65D-TU	TO-263	50pcs / Tube
7N65D-TR	TO-263	800pcs / 13"Reel
7N65N-TU	TO-251	75pcs / Tube
7N65M-TU	TO-252	75pcs / Tube
7N65M-TR	TO-252	2.5Kpcs / 13"Reel

ABSOLUTE MAXIMUM RATINGS

($T_c = 25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	7	A
Pulsed Drain Current (Note 2)	I_{DM}	28	A
Avalanche Energy	E_A	435	mJ
Power Dissipation	TO-220/TO-263/TO-262	P_D	142
	TO-251/TO-252		32
	ITO-220		48
Junction Temperature	T_J	+150	C
Storage Temperature	T_{STG}	-55 ~ +150	C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

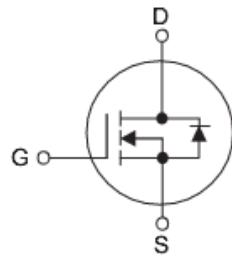
3. $L = 30mH$, $I_{AS} = 5.25A$, $V_{DD} = 50V$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ C$

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
650	1.5 @ $V_{GS} = 10V$	7



Block Diagram



Pin Definition:

1. Gate
2. Drain
3. Source

7N65 7N65F 7N65D 7N65E 7N65M 7N65N 650V N-Channel Power MOSFET

THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/ITO-220	R_{JA}	62.5	C/W
	TO-263/TO-262		110	
Junction to Case	TO-251/TO-252	R_{JC}	2.35	C/W
	TO-220/TO-263/TO-262		2.9	
	ITO-220		5.5	

ELECTRICAL CHARACTERISTICS $(T_c=25\text{ C}, \text{unless otherwise specified})$

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=650\text{V}, V_{GS}=0\text{V}$		1		μA
Gate- Source Leakage Current	Forward	I_{GSS}	$V_G=30\text{V}, V_{DS}=0\text{V}$		100	nA
	Reverse		$V_G=-30\text{V}, V_{DS}=0\text{V}$		-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	$I_D=250\mu\text{A}$, Referenced to 25°C	0.67			V/ C
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=3.5\text{A}$		1.35	1.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		1210	1400	pF
Output Capacitance	C_{oss}			140	180	pF
Reverse Transfer Capacitance	C_{rss}			40	50	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=300\text{V}, I_D=7\text{A}, R_G=25\Omega$ (Note 1, 2)		50	70	ns
Turn-On Rise Time	t_R			150	180	ns
Turn-Off Delay Time	$t_{D(OFF)}$			380	410	ns
Turn-Off Fall Time	t_F			180	220	ns
Total Gate Charge	Q_G	$V_{DS}=520\text{V}, I_D=7\text{A}, V_{GS}=10\text{V}$ (Note 1, 2)		29	38	nC
Gate-Source Charge	Q_{GS}			9		nC
Gate-Drain Charge	Q_{GD}			19		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_S=7\text{A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				7	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				28	A
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_S=7\text{A}$	490			ns
Reverse Recovery Charge	Q_{RR}	$dI/dt=100\text{A}/\mu\text{s}$ (Note 1)	3.2			μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by JH manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)